



# BZ03,BZ05,BZ10,BZ15

## GLASS PASSIVATED SILICON RECTIFIER DIODE

### Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: GJB33A-97, QZJ840611A, QZJ840611



### TECHNICAL DATA:

(Ta = 25°C )

Parameter name	Symbols	Unit	Specifications				Test Condition
			BZ03	BZ05	BZ10	BZ15	
Use for	Industrial frequency rectifier circuit.						
Store temperature	T	°C	-55~+150				
Quality Class			JP, JT, JCT, GS, G, G+				
Peak Repetitive Reverse Voltage	V <sub>RRM</sub>	V	50~1400				
Average Forward Current	I <sub>F(AV)</sub>	A	0.3	0.5	1.0	1.5	
Peak Forward Voltage	V <sub>FM</sub>	V	2.2				I=A I <sub>F(AV)</sub> , A=3.1415926
Average Forward Voltage	V <sub>F</sub>	V	1.2				I=I <sub>F(AV)</sub>
Non-repeat Forward Surge Current	I <sub>FSM</sub>	A	10	15	30	30	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I <sub>RM1</sub>	uA	10				V <sub>R</sub> =V <sub>RRM</sub> , Ta=25°C
Peak Reverse Current	I <sub>RM2</sub>	uA	200				V <sub>R</sub> =V <sub>RRM</sub> , Ta=125°C
Junction Temperature	T <sub>jm</sub>	°C	150				

### SPECIFICATIONS:

A	B	C	D	E	F	G	H	I	J
50V	100V	200V	300V	400V	600V	800V	1000V	1200V	1400V

### Outline and Dimensions:

#### Model Cross

BZ03(2CZ101), BZ05(2CZ102,2CZ54), BZ10(2CZ103,2CZ55,BZ6), BZ15(2CZ32)